Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A thin film forming method which makes a material, which becomes a source of thin films to be formed, particulate, introduces and deposits the particulate material on a first principal surface and a second principal surface, opposite to said first principal surface, of a substrate, and forms thin films simultaneously on the first principal surface and the second principal surface of the substrate, comprising exposing the first principal surface and the second principal surface of the substrate, and introducing the particulate material~~, including~~ with converging the particulate material and ~~increasing its~~ increasing the density ~~in the~~ of the particulate material by guides for introducing ~~of the~~ particulate material on the first principal surface and the second principal surface of the substrate.

2. (Canceled)

3. (Previously Presented) The thin film forming method according to claim 1, further including depositing the particulate material while rotating the substrate about a rotational axis that is normal to the first principal surface.

4. (Previously Presented) The thin film forming method according to claim 1, further including arranging heaters in a position facing the first principal surface and a position facing the second principal surface of the substrate and heating the substrate.

5 .(Previously Presented) The thin film forming method according to claim 1, further including generating the particulate material from a material used for formation of an oxide superconductor.

6. (Withdrawn - Previously Presented) A thin film forming apparatus which is equipped with a target made of a material which becomes a source of a thin film to be formed, a cathode for generating the material, which is particulate, from the target, a supporting member for supporting a substrate on which the particulate material is deposited, a heater for heating the substrate, and a guide for introducing the particulate material onto a first principal surface of the substrate and a second principal surface of the substrate, opposite to said first principal surface, further comprising said supporting member supporting the substrate so as to expose the first principal surface and the second principal surface of the substrate, and the guide being disposed in a position facing the first principal surface of the substrate and in a position facing the second principal surface of the substrate.

7. (Withdrawn - Previously Presented) The thin film forming apparatus according to claim 6, wherein the guide has an inclined portion spaced apart form the substrate by a distance that becomes shorter along a direction of the introducing of the particulate material.

8. (Withdrawn - Previously Presented) The thin film forming apparatus according to claim 6, wherein the supporting member comprises a rotating mechanism which rotates the substrate in a direction normal to the first principal surface of the substrate as an axis of rotation.

9. (Withdrawn) The thin film forming apparatus according to claim 6, wherein the heater is provided on a surface of each guide which faces the substrate.

10.(Withdrawn - Previously Presented) The thin film forming apparatus according to claim 6, wherein the target is arranged so that the particulate material may be incident onto the first principal surface or the second principal surface of the substrate at a predetermined angle.

11. (Withdrawn) The thin film forming apparatus according to claim 6, further including two or more of the targets.

12.(Withdrawn - Previously Presented) The thin film forming apparatus according to claim 6, wherein the target is made of a material used for formation of an oxide superconductor.